CMOS 8-BIT MICROCONTROLLER

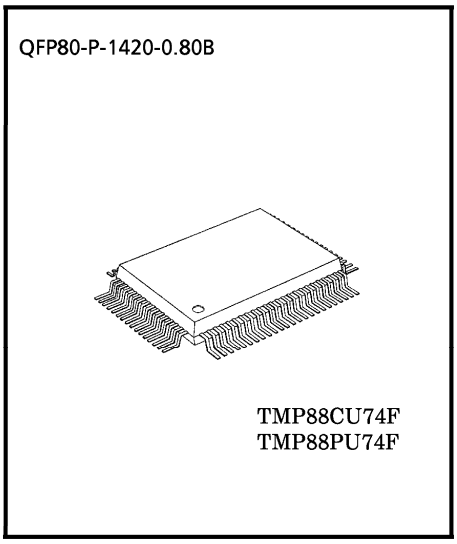
TMP88PU74F

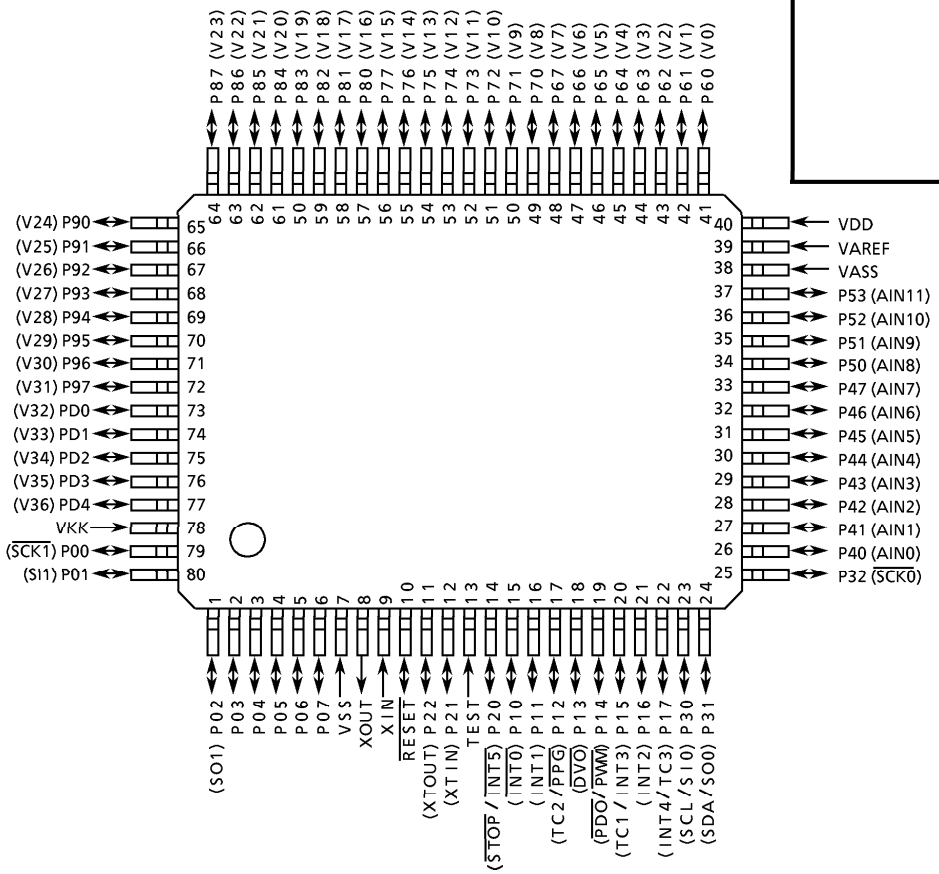
The 88PU74 are the high-speed and high performance 8-bit single chip microcomputers which built in a program storage area (96K byte) and the One-Time PROM of bector table storage area (256 byte). The 88PU74 is pin compatible with the 88CU74. The operations possible with the 88PU74 can be performed by writing programs to PROM. The 88PU74 can write and verify in the same way as the TC571000 an EPROM programmer.

PART No.	OTP	RAM	PACKAGE	ADAPTOR SOCKET
TMP88PU74F	96K byte + 256 byte	2K byte	QFP80-P-1420-0.80B	BM11131

PIN ASSIGNMENTS (TOP VIEW)

QFP80-P-1420-0.80B





PIN FUNCTION

The 88PU74 has two modes: MCU and PROM.

(1) MCU mode

In this mode, the 88PU74 is pin compatible with the 88CU74 (fix the TEST pin at low level).

(2) PROM mode

PIN NAME (PROM mode)	INPUT/OUTPUT	FUNCTIONS	PIN NAME (MCU mode)
A16	Input	PROM address inputs	P60
A15 to A8			P05, P32 to 30, P53 to 50
A7 to A0			P47 to P40
D7 to D0	I/O	PROM data input/outputs	P17 to P10
$\overline{CE}$	Input	Chip enable signal input (active low)	P03
$\overline{OE}$		Output enable signal input (active low)	P04
$\overline{PGM}$		Program mode single input	P02
VPP	Power supply	+ 12.75 V / 5 V (Program supply voltage)	TEST
VCC		+ 6.25 V / 5 V	VDD
GND		0 V	VSS
P37 to P30	Input	Pull-up with resistance for input processing	
P47 to P41			
P54 to P50			
P01		PROM mode setting pin. Be fixed at high level.	
P21			
P07, P06, P00		PROM mode setting pin. Be fixed at low level.	
P22 , P20			
$\overline{RESET}$			
P67 to P61	Output	Open	
P77 to P70			
P87 to P80			
P97 to P90			
PD4 to PD0			
XIN	Input	Connect an 10 MHz oscillator to stabilize the internal state.	
XOUT	Output		
VAREF	Power supply	0 V (GND)	
VASS			
VKK		Open	

OPERATIONAL DESCRIPTION

The configuration and functions of the 88PU74 are the same as those of the 88CU74, except in that a one-time PROM is used instead of an on-chip mask ROM.

1. OPERATING MODE

The 88PU74 has two modes: MCU and PROM.

1.1 MCU Mode

The MCU mode is activated by fixing the TEST / VPP pin at low level.

In the MCU mode, operation is the same as with the 88CU74 (the TEST / VPP pin cannot be used open because it has no built-in pull-down resistance).

1.1.1 Program Memory

The 88PU74 has a 96K byte (addresses 04000_H to $1BFFF_H$ in the MCU mode, addresses 00000_H to $17FFF_H$ in the PROM mode) of program storage area and 256 byte (addresses FFF00 to $FFFFF_H$ in the MCU mode, addresses 1FF00 to $1FFFF_H$ in the PROM mode) one-time PROM of vector table storage area.

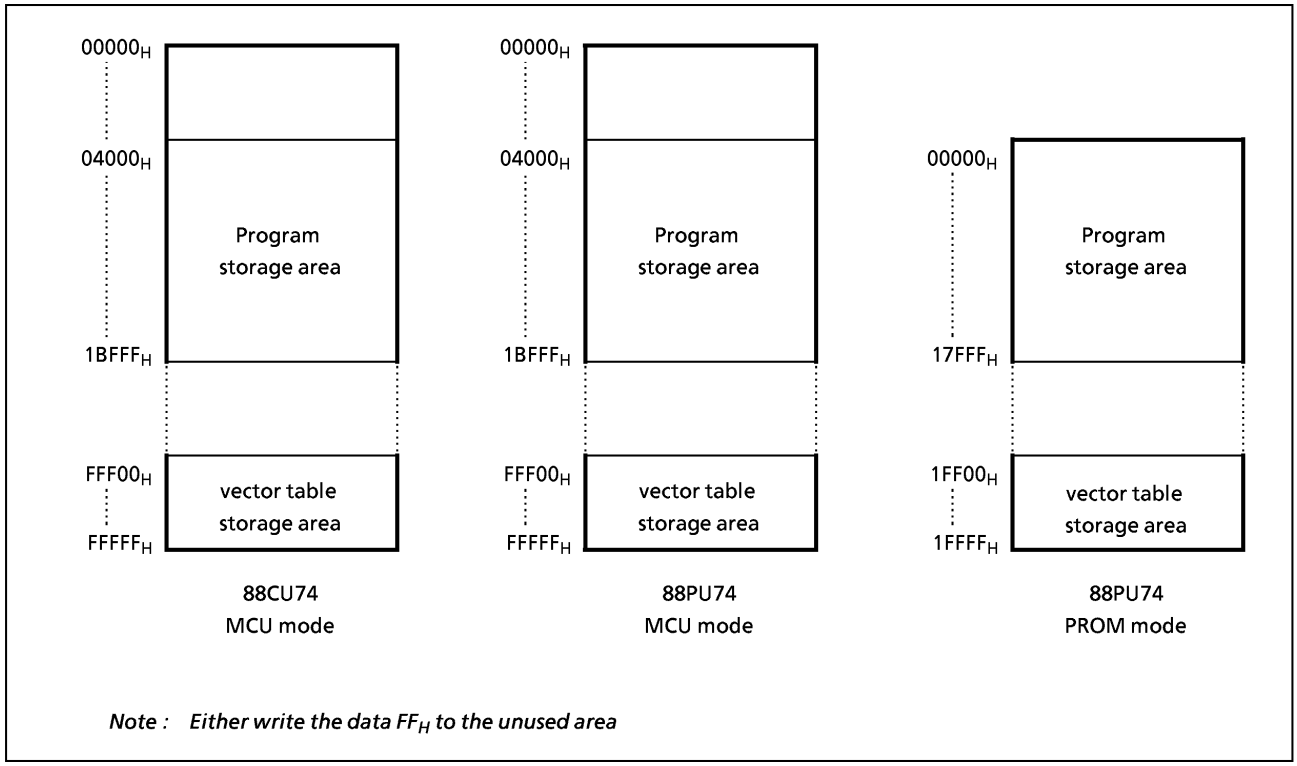


Figure 1-1. Program Storage Area

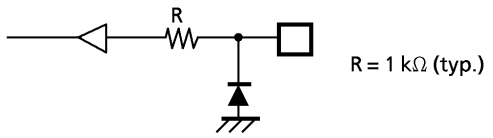
1.1.2 Data Memory

The 88PU74 has an on-chip 2k byte data memory (static RAM).

1.1.3 Input/Output Circuitry

(1) Control pins

The control pins of the 88PU74 are the same as those of the 88CU74 except that the TEST pin has is no built-in pull-down resistance.



Note : TEST pin has no built-in pull-down resistance

Figure 1-2. TEST Pin

(2) I/O ports

The I/O circuitries of 88PU74 I/O ports are the same as the code A type I/O circuitries of the 88CU74.

1.2 PROM Mode

The PROM mode is activated by setting shown in Figure 1-2. The PROM mode is used to write and verify programs with a general-purpose PROM programmer. The high-speed programming mode can be used for program operation.

The 88PU74 is not supported an electric signature mode, so the ROM type must be set to TC571000.

Set the adaptor socket switch to "N".

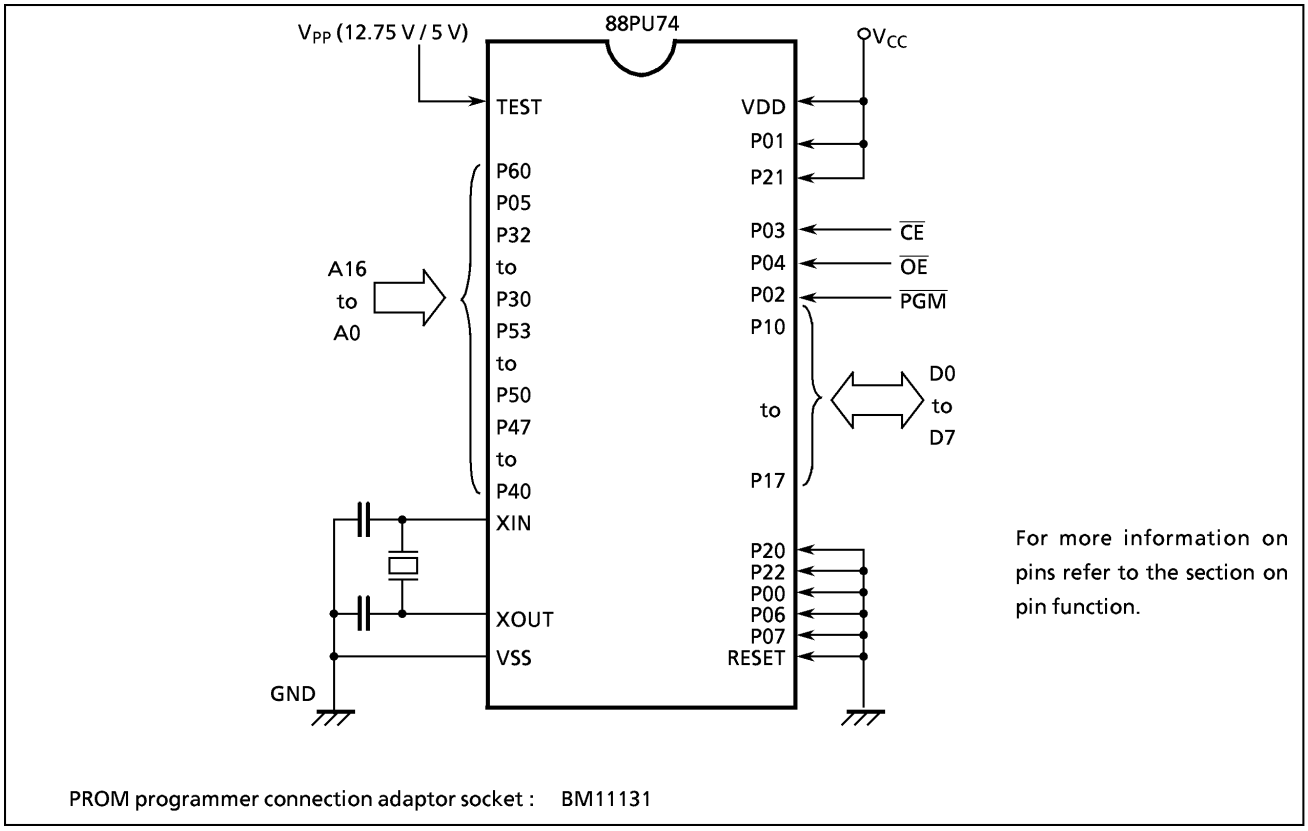


Figure 1-3. Setting for PROM Mode

1.2.1 Programming Flowchart (High-speed Programming)

The high-speed programming mode is achieved by applying the program voltage (+ 12.75 V) to the Vpp pin when Vcc = 6.25 V. After the address and input data are stable, the data is programmed by applying a single 0.1ms program pulse to the $\overline{CE}$ input. The programmed data is verified. If incorrect, another 0.1ms program pulse is applied and then the programmed data is verified. This process should be repeated (up to 25 times) until the program operates correctly. After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with Vcc = Vpp = 5 V.

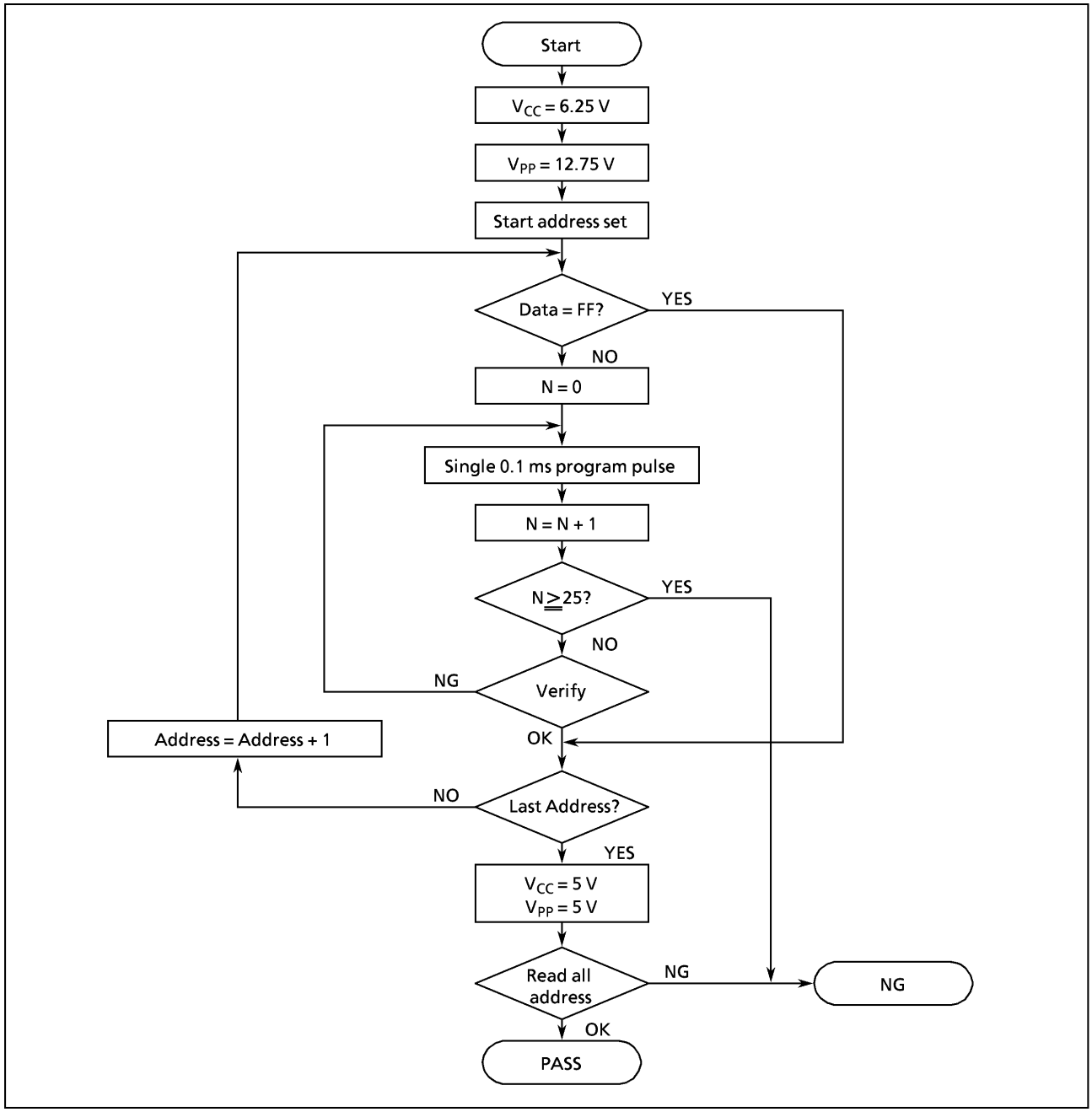


Figure 1-4. Flowchart of High-speed Programming

1.2.2 Writing Method for General-purpose PROM Program

(1) Adapters
BM11131

(2) Adapter setting
Switch (SW1) is set to side N.

(3) PROM programmer specifying
i) PROM type is specified to TC571000.
Writing voltage: 12.75 V (high-speed program)

ii) Data transfer (copy) (note 1)
In TMP88PU74, EPROM is within the addresses 0000_H to $7FFF_H$. Data is required to be transferred (copied) to the addresses where it is possible to write. The program area in MCU mode and PROM mode is referred to "Program memory area" in Figure 1-1.

Ex. In the block transfer (copy) mode, executed as below.
Program area : transferred addresses 04000_H to $1BFFF_H$ to addresses 00000 to $17FFF_H$
Vector area : transferred addresses $FFF00_H$ to $FFFFF_H$ to 1FF00 to $1FFFFF_H$

iii) Writing address is specified. (note 1)
Start address : 0000_H
End address : $1FFFF_H$

(4) Writing
Writing/Verifying is required to be executed in accordance with PROM programmer operating procedure.

Note 1 : The specifying method is referred to the PROM programmer description. Either write the data FF_H to the unused area or set the PROM programmer to access only the program storage area.

Note 2 : When MCU is set to an adapter or the adapter is set to PROM programmer, a position of pin 1 must be adjusted. If the setting is reversed, MCU, the adapter and PROM program is damaged.

Note 3 : The TMP88PU74 does not support the electric signature mode (hereinafter referred to as "signature"). If the signature is used in PROM program, a device is damaged due to applying 12V ± 0.5V to the address pin 9 (A9). The signature must not be used.

ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (V_{SS} = 0 V)

PARAMETER	SYMBOL	PINS	RATINGS	UNIT
Supply Voltage	V_{DD}		– 0.3 to 6.5	V
Program Voltage	V_{PP}	TEST / VPP	– 0.3 to 13.0	V
Input Voltage	V_{IN}		– 0.3 to V_{DD} + 0.3	V
Output Voltage	V_{OUT1}	P2, P3 (at open drain)	– 0.3 to V_{DD} + 0.3	V
	V_{OUT2}	P6, P7, P8, P9, PD	V_{DD} – 40 to V_{DD} + 0.3	
Output Current (Per 1 pin)	I_{OUT1}	P0, P1, P2, P4, P5	3.2	mA
	I_{OUT2}	P6, P7, P8, P9, PD	– 25	
Output Current (Total)	ΣI_{OUT1}	P0, P1, P2, P3, P4, P5	– 40	mA
	ΣI_{OUT2}	P0, P1, P2, P3, P4, P5	120	
	ΣI_{OUT3}	P6, P7, P8, P9, PD	– 160	
Power Dissipation [Topr = 25 °C]	PD	note	1200	mW
Soldering Temperature (time)	Tsld		260 (10 s)	°C
Storage Temperature	Tstg		– 55 to 125	°C
Operating Temperature	Topr		– 30 to 70	°C

Note : Power Dissipation (PD) ; For PD, it is necessary to decrease 14.3 mW/°C. (Refernce to TMP88CU74)

RECOMMENDED OPERATING CONDITIONS (V_{SS} = 0 V, Topr = – 30 to 70 °C)

PARAMETER	SYMBOL	PINS	CONDITIONS		Min.	Max.	UNIT
Supply Voltage	V_{DD}		fc = 12.5 MHz	NORMAL1, 2 modes	4.5	5.5	V
				IDLE1, 2 modes			
			fs = 32.768 kHz	SLOW mode	2.7		
				SLEEP mode			
				STOP mode	2.0		
Input High Voltage	V_{IH1}	Except hysteresis input	$V_{DD} \geqq 4.5$ V		$V_{DD} \times 0.70$	V_{DD}	V
	V_{IH2}	Hysteresis input			$V_{DD} \times 0.75$		
	V_{IH3}		$V_{DD} < 4.5$ V		$V_{DD} \times 0.90$		
Input Low Voltage	V_{IL1}	Except hysteresis input	$V_{DD} \geqq 4.5$ V		0	$V_{DD} \times 0.30$	V
	V_{IL2}	Hysteresis input				$V_{DD} \times 0.25$	
	V_{IL3}		$V_{DD} < 4.5$ V			$V_{DD} \times 0.10$	
Clock Frequency	fc	XIN, XOUT	V_{DD} = 4.5 V to 5.5 V Note)		8	12.5	MHz
		XTIN, XTOUT	V_{DD} = 2.7 V to 5.5 V		30.0	34.0	kHz

Note : Clock frequency fc : Supply voltage range is specified in NORMAL 1/2 mode and IDLE 1/2 mode.

D.C. CHARACTERISTICS

(V_{SS} = 0 V, Topr = – 30 to 70 °C)

PARAMETER	SYMBOL	PINS	CONDITIONS	Min.	Typ.	Max.	UNIT
Hysteresis Voltage	V_{HS}	Hysteresis input		–	0.9	–	V
Input Current	I_{IN1}	TEST	V_{DD} = 5.5 V V_{IN} = 5.5 V / 0 V	–	–	± 2	μA
	I_{IN2}	Open drain ports, Tri-state ports					
	I_{IN3}	$\overline{RESET}$, $\overline{STOP}$					
Input Resistance	R_{IN3}	$\overline{RESET}$		100	220	450	kΩ
Pull-down Resistance	R_K	Source open drain ports	V_{DD} = 5.5 V, V_{KK} = – 30 V	50	80	110	
Output Leakage Current	I_{LO1}	Sink open drain ports	V_{DD} = 5.5 V, V_{OUT} = 5.5 V	–	–	2	μA
	I_{LO2}	Source open drain ports	V_{DD} = 5.5 V, V_{OUT} = – 32 V	–	–	– 2	
	I_{LO3}	Tri-state ports	V_{DD} = 5.5 V, V_{OUT} = 5.5 V / 0 V	–	–	2	
Output High Voltage	V_{OH2}	Tri-state ports	V_{DD} = 4.5 V, I_{OH} = – 0.7 mA	4.1	–	–	V
Output Low Voltage	V_{OL}	Except XOUT	V_{DD} = 4.5 V, I_{OL} = 1.6 mA	–	–	0.4	V
Output High current	I_{OH}	P6, P7, P8, P9, PD port	V_{DD} = 4.5 V, V_{OH} = 2.4 V	–	– 20	–	mA
Supply Current in NORMAL 1, 2 modes	I_{DD}		V_{DD} = 5.5 V V_{IN} = 5.3 V / 0.2 V fc = 12.5 MHz fs = 32.768 kHz	–	18	–	mA
Supply Current in IDLE 1, 2 modes				–	9	–	
Supply Current in SLOW mode			V_{DD} = 3.0 V V_{IN} = 2.8 V / 0.2 V fs = 32.768 kHz	–	30	60	μA
Supply Current in SLEEP mode				–	15	30	μA
Supply Current in STOP mode			V_{DD} = 5.5 V V_{IN} = 5.3 V / 0.2 V	–	0.5	10	μA

Note 1 : Typical values show those at Topr = 25 °C , V_{DD} = 5V.

Note 2 : Input Current I_{IN3} ; The current through resistor is not included, when the input resistor (pull-up/pull-down) is contained.

A/D CONVERSION CHARACTERISTICS

(V_{SS} = 0 V, V_{DD} = 4.5 to 5.5 V, Topr = – 30 to 70 °C)

PARAMETER	SYMBOL	CONDITIONS	Min.	Typ.	Max.	UNIT
Analog Reference Voltage	V_{AREF}		4.5	–	V_{DD}	V
	V_{ASS}		V_{SS}			
Analog Reference Voltage Range	V_{AIN}		V_{ASS}	–	V_{AREF}	V
Analog Input Voltage	I_{REF}	V_{AREF} = 5.5 V, V_{ASS} = 0.0 V	–	0.5	1.0	mA
Nonlinearity Error		V_{DD} = 5.0 V, V_{SS} = 0.0 V V_{AREF} = 5.000 V V_{ASS} = 0.000 V	–	–	± 1	LSB
Zero Point Error			–	–	± 1	
Full Scale Error			–	–	± 1	
Total Error			–	–	± 2	

Note : Quantizing error is not contained in those errors.

A.C. CHARACTERISTICS

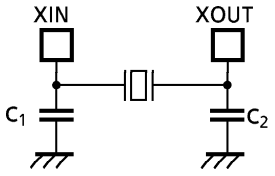
(V_{SS} = 0 V, V_{DD} = 4.5 to 5.5 V, Topr = – 30 to 70 °C)

PARAMETER	SYMBOL	CONDITIONS	Min.	Typ.	Max.	UNIT
Machine Cycle Time	tcy	In NORMAL1, 2 modes	0.32	–	0.5	μs
		In IDLE1, 2 modes				
		In SLOW mode	117.6	–	133.3	
		In SLEEP mode				
High Level Clock Pulse Width	t_{WCH}	For external clock operation (XIN input), fc = 16 MHz	70	–	–	ns
Low Level Clock Pulse Width	t_{WCL}					
High Level Clock Pulse Width	t_{WSH}	For external clock operation (XTIN input), fs = 32.768 kHz	14.7	–	–	μs
Low Level Clock Pulse Width	t_{WSL}					

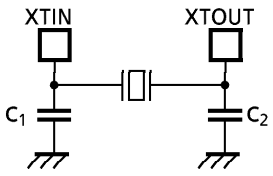
RECOMMENDED OSCILLATING CONDITIONS

(V_{SS} = 0 V, V_{DD} = 4.5 to 5.5 V, Topr = – 30 to 70 °C)

PARAMETER	Oscillator	Oscillation Frequency	Recommended Oscillator		Recommended Constant C_1	Recommended Constant C_2
High-frequency Oscillation	Ceramic Resonator	12.5 MHz	Murata	CSA12.5MTZ	30 pF	30 pF
		8 MHz	Murata	CSA8.00MTZ	30 pF	30 pF
	Crystal Oscillator	12.5 MHz	NDK	AT-51	10 pF	10 pF
Low-frequency Oscillation	Crystal Oscillator	32.768 kHz	NDK	MX-38T	15 pF	15 pF



(1) High-frequency Oscillation



(2) Low-frequency Oscillation

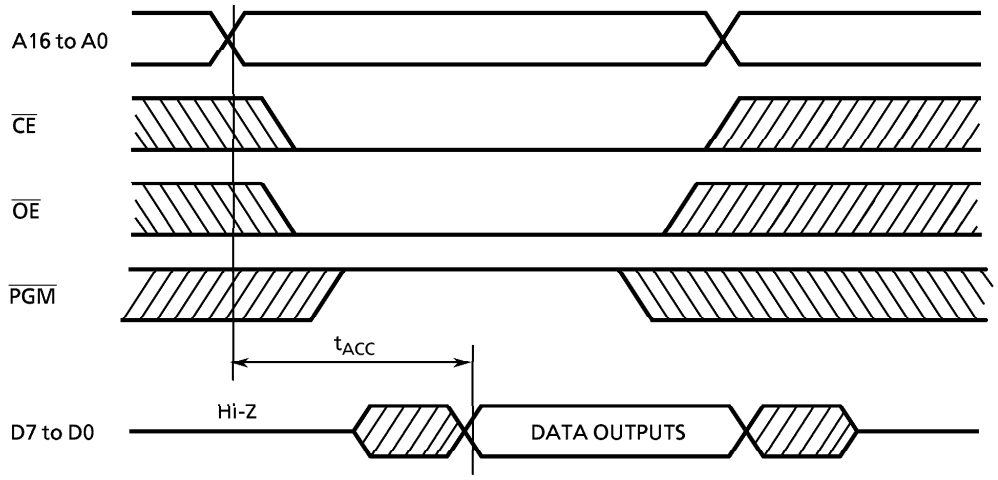
Note : An electrical shield by metal shied plate on the IC package should be recommend able in order to prevent the device from the high electric fieldstress applied for continuous reliable operation.

D.C./A.C. CHARACTERISTICS (PROM mode) (V_{SS} = 0 V)

(1) Read Operation (VDD = 5.0 ± 0.25 V, Topr = 25 ± 5 °C)

PARAMETER	SYMBOL	CONDITIONS	Min.	Typ.	Max.	UNIT
Input High Voltage (A0 to A16, $\overline{CE}$, $\overline{OE}$, $\overline{PGM}$)	V_{IH4}		VDD × 0.7	–	VDD	V
Input Low Voltage (A0 to A16, $\overline{CE}$, $\overline{OE}$, $\overline{PGM}$)	V_{IL4}		0	–	0.8	V
Program Power Supply Voltage	V_{PP}		4.75	5.0	5.25	V
Address Access Time	t_{ACC}		–	1.5tcyc + 300	–	ns

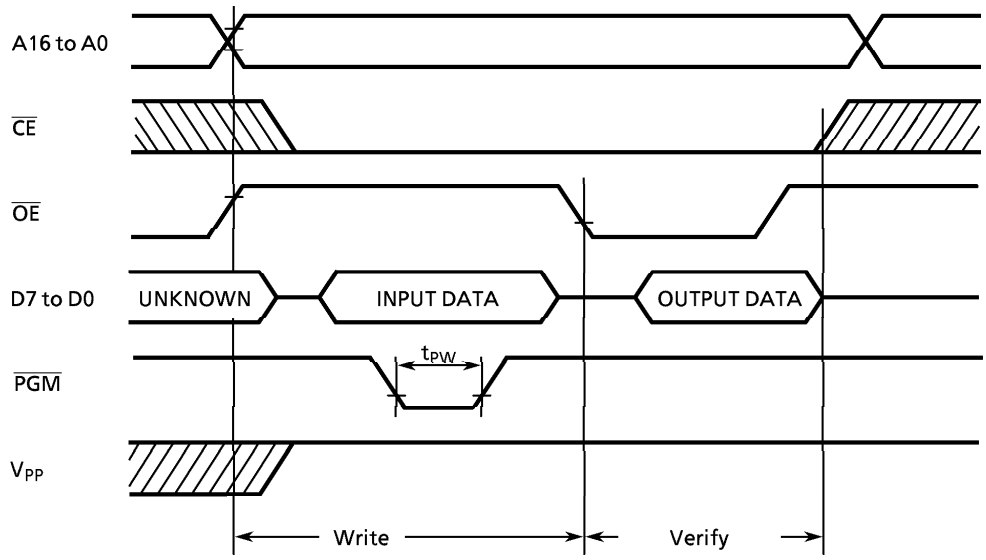
Note : tcyc = 400 ns at 10 MHz



(2) High-Speed Programming Operation (Topr = 25 ± 5 °C, VDD = 6.25 ± 0.25 V)

PARAMETER	SYMBOL	CONDITIONS	Min.	Typ.	Max.	UNIT
Input High Voltage (D0 to D7, A0 to A16, $\overline{CE}$, $\overline{OE}$, $\overline{PGM}$)	V_{IH4}		VDD × 0.7	–	VDD	V
Input Low Voltage (D0 to D7, A0 to A16, $\overline{CE}$, $\overline{OE}$, $\overline{PGM}$)	V_{IL4}		0	–	0.8	V
Program Power Supply Voltage	V_{PP}		12.5	12.75	13.0	V
Initial Program Pulse Width	t_{PW}	V_{DD} = 6.0 V	0.095	0.1	0.105	ms

High-program



Note1 : When V_{CC} power supply is turned on or after, V_{pp} must be increased.
When V_{CC} power supply is turned off or before, V_{pp} must be decreased.

Note2 : The device must not be set to the EPROM programmer or picked up from it under applying the program voltage (12.75V ± 0.5V) to the V_{pp} pin as the device is damaged.

Note3 : Be sure to execute the recommended programing mode with the recommended programing adaptor. If a mode or an adaptor except the above, the misoperation sometimes occurs.